

7A, 600V N-CHANNEL MOSFET

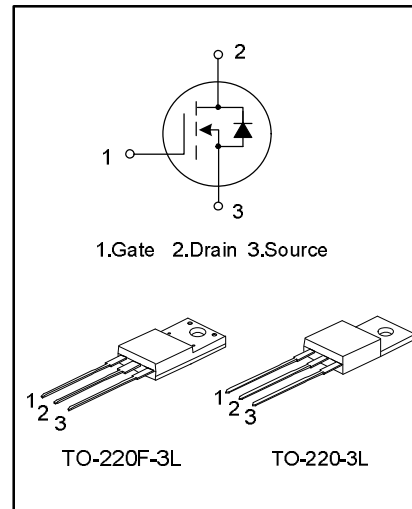
GENERAL DESCRIPTION

SVD7N60T/F is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary S-Rin™ structure DMOS technology. The improved planar stripe cell and the improved guarding ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.

FEATURES

- * 7A,600V, $R_{DS(on)}$ (typ) =0.96 Ω @ $V_{GS}=10V$
- * Low gate charge
- * Low C_{rss}
- * Fast switching
- * Improved dv/dt capability



ORDERING SPECIFICATIONS

Part No.	Package	Marking	Shipping
SVD7N60T	TO-220-3L	SVD7N60T	50Unit/Tube
SVD7N60F	TO-220F-3L	SVD7N60F	50Unit/Tube

ABSOLUTE MAXIMUM RATINGS ($T_c=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	SVD7N60T	SVD7N60F	Unit
Drain-Source Voltage	V_{DS}	600		V
Gate-Source Voltage	V_{GS}	± 30		V
Drain Current	I_D	7.0		A
Drain Current Pulsed	I_{DM}	28		A
Power Dissipation($T_c=25^{\circ}C$) -Derate above $25^{\circ}C$	P_D	147	48	W
		1.18	0.38	W/ $^{\circ}C$
Single Pulsed Avalanche Energy (Note 1)	EAS	530		mJ
Repetitive Avalanche Energy	EAR	14.2		mJ
Operation Junction Temperature	T_J	$-55 \sim +150$		$^{\circ}C$
Storage Temperature	T_{stg}	$-55 \sim +150$		$^{\circ}C$

THERMAL CHARACTERISTICS

Parameter	Symbol	SVD7N60T	SVD7N60F	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	0.85	2.6	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BVDSS	V _{GS} =0V, I _D =250μA	600	--	--	V
Breakdown Voltage Temperature coefficient	ΔBVDSS/ ΔT _j	I _D =250uA, referenced to 25°C	--	0.72	--	V/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V	--	--	10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	2.0	--	4.0	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3.5A	--	0.96	1.2	Ω
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	--	1095	1430	pF
Output Capacitance	C _{oss}		--	93	175	
Reverse Transfer Capacitance	C _{rss}		--	2	21	
Turn-on Delay Time	t _{d(on)}	V _{DD} =300V, I _D =7.0A, R _G =25Ω (Note 2,3)	--	39	60	ns
Turn-on Rise Time	t _r		--	29	70	
Turn-off Delay Time	t _{d(off)}		--	248	300	
Turn-off Fall Time	t _f		--	36	90	
Total Gate Charge	Q _g	V _{DS} =480V, I _D =7.0A, V _{GS} =10V (Note 2,3)	--	26.8	37	nC
Gate-Source Charge	Q _{gs}		--	5.1	--	
Gate-Drain Charge	Q _{gd}		--	8.5	--	

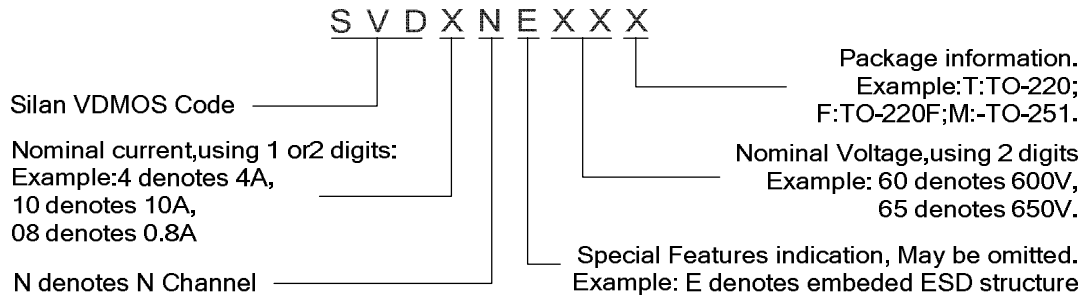
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I _S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	7.0	A
Pulsed Source Current	I _{SM}		--	--	28	
Diode Forward Voltage	V _{SD}	I _S =7.0A, V _{GS} =0V	--	--	1.4	V
Reverse Recovery Time	T _{rr}	I _S =7.0A, V _{GS} =0V, dI _F /dt=100A/μS	--	365	--	ns
Reverse Recovery Charge	Q _{rr}		--	3.4	--	μC

Notes:

1. L=19.5mH, I_{AS}=7.0A, V_{DD}=50V, R_G=25Ω, starting T_J=25°C;
2. Pulse Test: Pulse width ≤300μs, Duty cycle≤2%;
3. Essentially independent of operating temperature.

NOMENCLATURE



TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

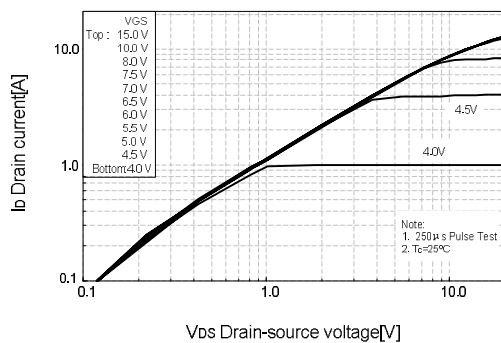


Figure 2. Transfer Characteristics

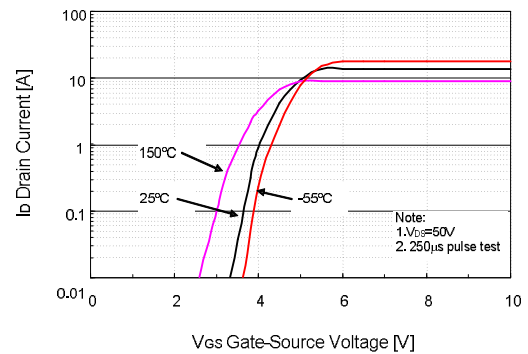


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

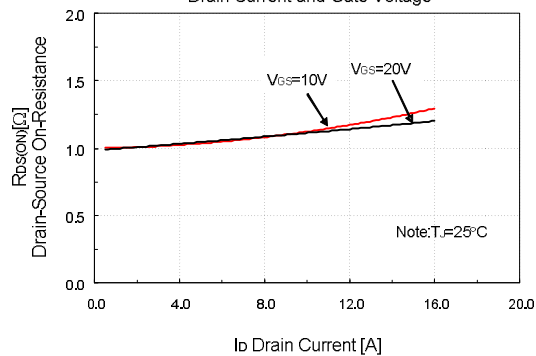
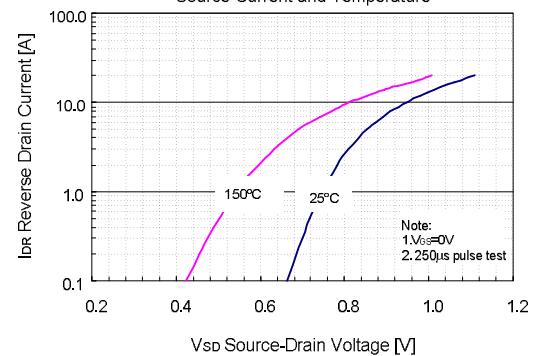


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



TYPICAL CHARACTERISTICS (continued)

Figure 5. Capacitance Characteristics

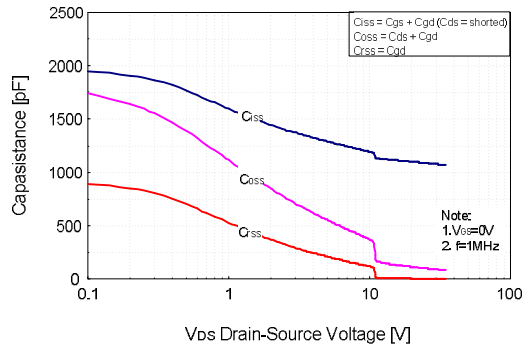


Figure 6. Gate Charge Characteristics

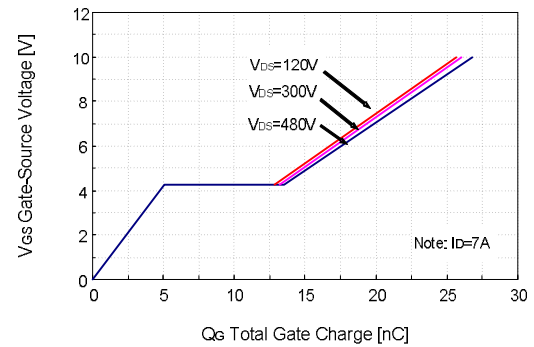


Figure 7. Breakdown Voltage Variation vs. Temperature

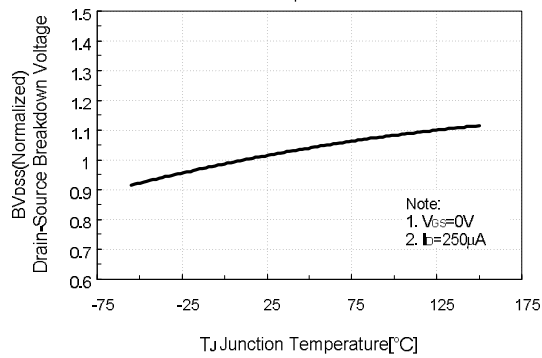
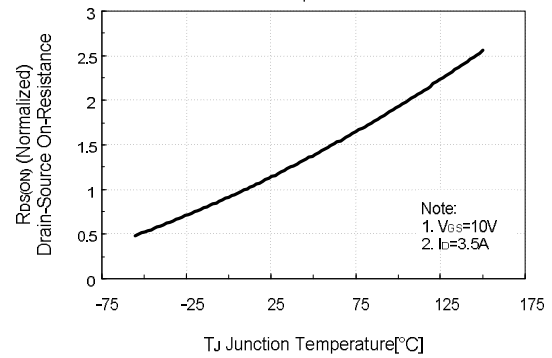
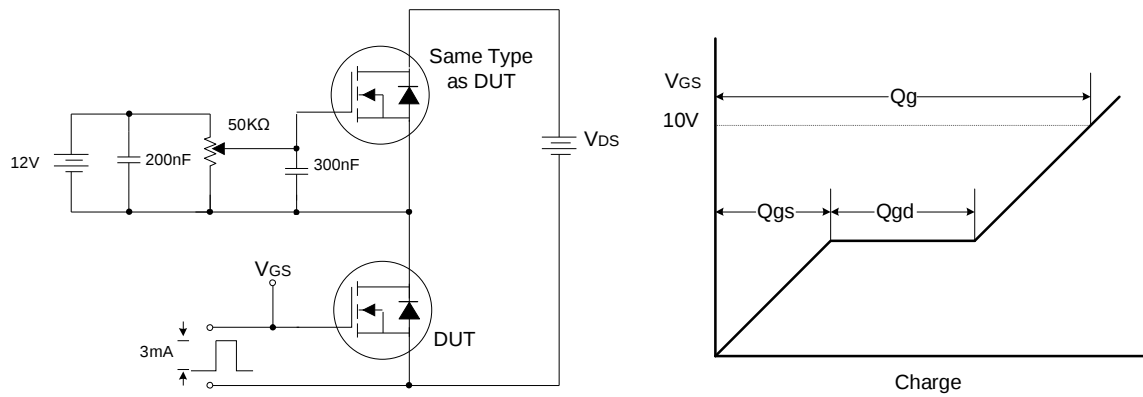


Figure 8. On-resistance Variation vs Temperature

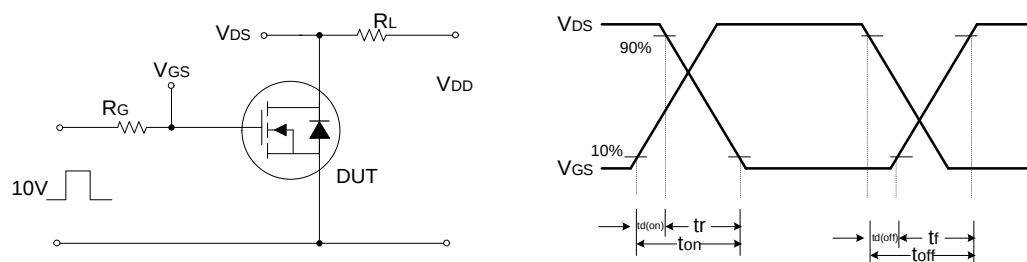


TYPICAL TEST CIRCUIT

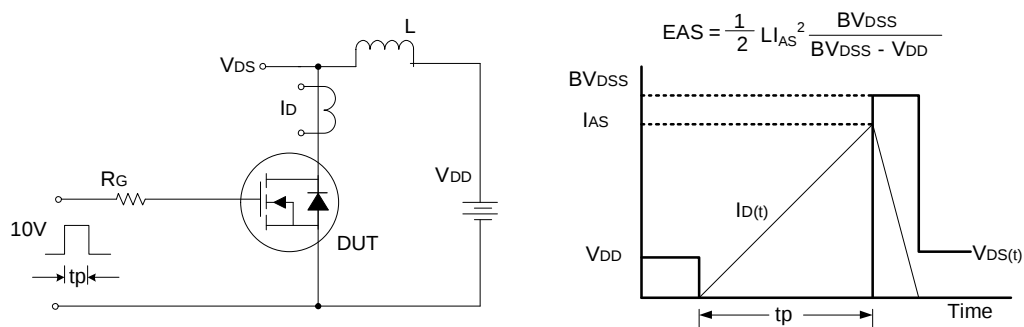
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



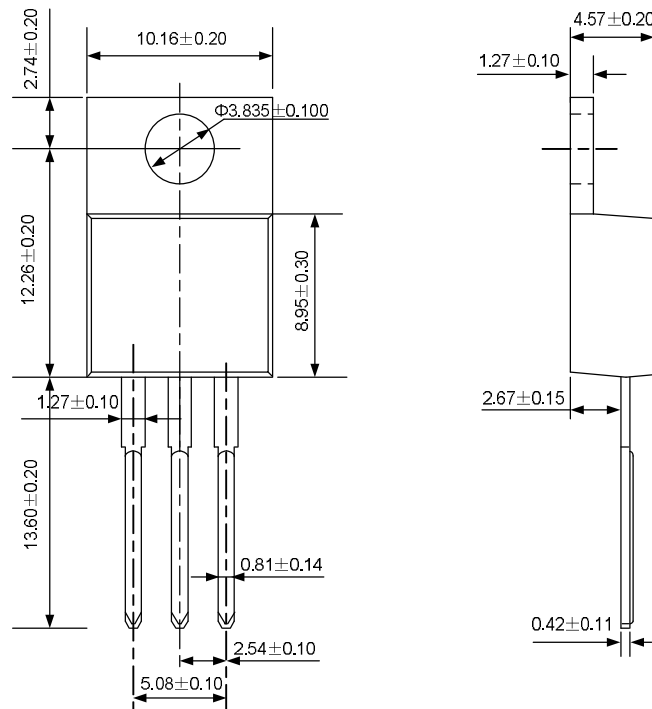
Unclamped Inductive Switching Test Circuit & Waveform



PACKAGE OUTLINE

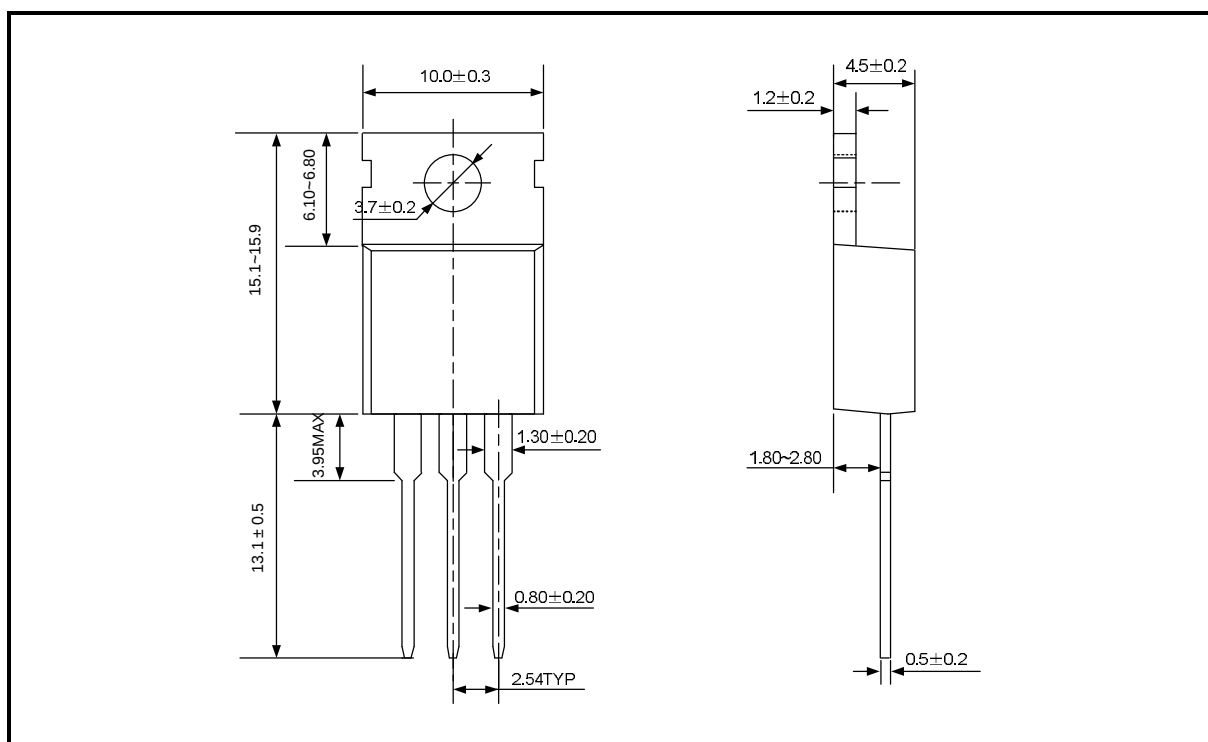
TO-220-3L(One)

UNIT:
mm



TO-220-3L (Two)

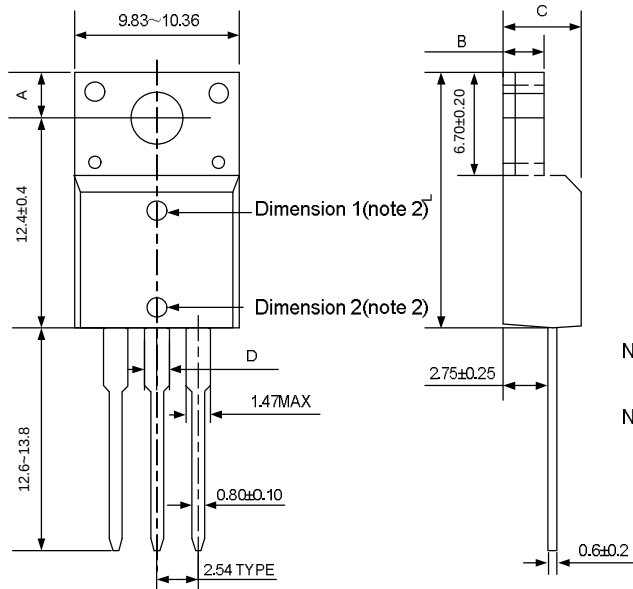
UNIT:
mm



PACKAGE OUTLINE (continued)

TO-220F-3L(One)

UNIT: mm



Symbol(note1)	Dimension1	Dimension2
A	3.30 ± 0.15	2.70 ± 0.15
B	2.55 ± 0.20	3.0 ± 0.20
C	4.72 ± 0.2	4.50 ± 0.20
D	1.47 MAX	1.75 MAX
L	15.75 ± 0.30	15.00 ± 0.30

Note1: There may be two values for some products due to different plastic mould machine, so two dimensions of the same position are listed;

Note2: When the product size is Dimension1, the thimble hole is on top of the surface; when the size is Dimension2, the center hole is on bottom of the surface.

TO-220F-3L (Two)

UNIT: mm

